

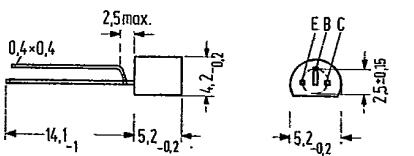
SIEMENS AKTIENGESELLSCHAFT 25C 04190

D

BC 546, BC 547, BC 548, BC 549 and BC 550 are epitaxial NPN silicon planar transistors in TO 92 plastic packages (10 A 3 DIN 41868). They are intended for use in AF input and driver stages (BC 549; BC 550 for low-noise input stages) and as complementary transistors to BC 556, BC 557, BC 558, BC 559 and BC 560.

Type	Ordering code
BC 546 <sup>1)</sup>	Q62702-C687
BC 546 VI	Q62702-C687-V3
BC 546 A	Q62702-C687-V1
BC 546 B	Q62702-C687-V2
BC 547 <sup>1)</sup>	Q62702-C688
BC 547 VI	Q62702-C688-V3
BC 547 A	Q62702-C688-V1
BC 547 B	Q62702-C688-V2
BC 548 <sup>1)</sup>	Q62702-C689
BC 548 VI	Q62702-C689-V4
BC 548 A	Q62702-C689-V1
BC 548 B	Q62702-C689-V2
BC 548 C	Q62702-C689-V3

Type	Ordering code
BC 549 <sup>1)</sup>	Q62702-C690
BC 549 B	Q62702-C690-V1
BC 549 C	Q62702-C690-V2
BC 550 <sup>1)</sup>	Q62702-C691
BC 550 B	Q62702-C691-V1
BC 550 C	Q62702-C691-V2



Mounting instruction: Fixing hole dia 0.6  
Approx. weight 0.25 g Dimensions in mm

#### Maximum ratings

	BC 546	BC 547	BC 548	BC 549	BC 550	
Collector-base voltage	80	50	30	30	50	V
Collector-emitter voltage	80	50	30	30	50	V
Collector-emitter voltage	65	45	30	30	45	V
Emitter-base voltage	6	6	5	5	5	V
Collector current	$I_C$	100	100	100	100	mA
Collector peak current	$I_{CM}$	200	200	200	200	mA
Base peak current	$I_{BM}$	200	200	200	200	mA
Emitter-peak current	$I_{EM}$	200	200	200	200	mA
Junction temperature	$T_j$	150	150	150	150	°C
Storage temperature range	$T_{stg}$	-65 to +150				°C
Total power dissipation ( $T_{amb} = 25^\circ\text{C}$ )	$P_{tot}$	500	500	500	500	mW

#### Thermal resistance

Junction to ambient air	$R_{thJA}$	$\leq 250$	$\leq 250$	$\leq 250$	$\leq 250$	K/W
Junction to case	$R_{thJC}$	$\leq 150$	$\leq 150$	$\leq 150$	$\leq 150$	K/W

1) If the order does not include any exact indication of the current amplification group desired, a transistor of a current amplification group just available from stock will be delivered.

**Static characteristics ( $T_{\text{amb}} = 25^\circ\text{C}$ )**

The transistors are grouped in accordance with the DC current gain  $h_{\text{FE}}$  and are marked by A, B, and C. At  $V_{\text{CE}} = 5 \text{ V}$  and the collector currents tabulated below the following static characteristics apply.

Type	BC 546 BC 547 BC 548	BC 546 BC 547 BC 548	BC 546 BC 547, BC 549 BC 548, BC 550	BC 548, BC 549, BC 550
$h_{\text{FE}}$ group	VI	A	B	C
$I_C$ mA	$h_{\text{FE}}$ $I_C/I_B$	$h_{\text{FE}}$ $I_C/I_B$	$h_{\text{FE}}$ $I_C/I_B$	$h_{\text{FE}}$ $I_C/I_B$
0.01 2 100	110 (75 to 150)	90 180 (110 to 220)	150 290 (200 to 450)	270 500 (420 to 800)
		120	200	400

Collector cutoff current ( $V_{\text{CBO}} = 30 \text{ V}$ )	$I_{\text{CBO}}$	$\leq 15$	nA
Collector cutoff current ( $V_{\text{CBO}} = 30 \text{ V}; T_{\text{amb}} = 150^\circ\text{C}$ )	$I_{\text{CBO}}$	$\leq 5$	$\mu\text{A}$
Collector-emitter saturation voltage ( $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ )	$V_{\text{CEsat}}$	90 (< 250)	mV
( $I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$ )	$V_{\text{CEsat}}$	200 (< 600)	mV
( $I_C = 10 \text{ mA}$ ) <sup>1)</sup>	$V_{\text{CEsat}}$	300 (< 600)	mV
Base-emitter saturation voltage <sup>2)</sup> ( $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ )	$V_{\text{BEsat}}$	700	mV
( $I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$ )	$V_{\text{BEsat}}$	900	mV
Base-emitter voltage ( $V_{\text{CE}} = 5 \text{ V}; I_C = 2 \text{ mA}$ )	$V_{\text{BE}}$	660 (580 to 700)	mV
Base-emitter voltage ( $V_{\text{CE}} = 5 \text{ V}; I_C = 10 \text{ mA}$ )	$V_{\text{BE}}$	< 720	mV

1) For the characteristic which passes through the point  $I_C = 11 \text{ mA}; V_{\text{CE}} = 1 \text{ V}$  at constant base current.

2)  $\frac{\Delta V_{\text{BEsat}}}{\Delta T_i}$  approx. =  $1.7 \text{ mV/K}$ ;  $\frac{\Delta V_{\text{BE}}}{\Delta T_i}$  approx. =  $-2 \text{ mV/K}$

25C D 8235605 0004192 3 SIEG

T-29-21

BC 546 - BC 550

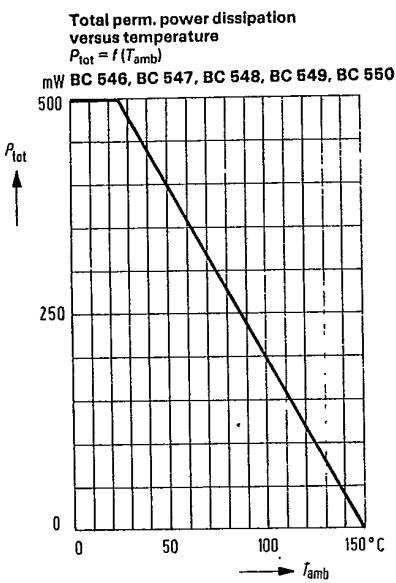
SIEMENS AKTIENGESELLSCHAFT

Dynamic characteristics ( $T_{amb} = 25^\circ C$ )		BC 546 BC 547 BC 548	BC 549	BC 550	
Transition frequency ( $V_{CE} = 5 V$ ; $I_C = 10 \mu A$ ; $f = 100 \text{ MHz}$ )	$f_T$	300	300	300	MHz
Collector-base capacitance ( $V_{CBO} = 10 V$ ; $f = 1 \text{ MHz}$ )	$C_{CBO}$	2.5 (<4.5)	2.5 (<4.5)	2.5 (<4.5)	pF
Emitter-base capacitance ( $V_{EBO} = 0.5 V$ ; $f = 1 \text{ MHz}$ )	$C_{EBO}$	9	9	9	pF
Noise figure ( $V_{CE} = 5 V$ ; $I_C = 200 \mu A$ ; $R_g = 2 k\Omega$ ; $f = 1 \text{ kHz}$ ; $\Delta f = 200 \text{ Hz}$ )	$NF$	2 (<10)	1.2 (<4)	1 (<4)	dB
Equivalent noise voltage ( $V_{CE} = 5 V$ ; $I_C = 200 \mu A$ ; $R_g = 2 k\Omega$ ; $f = 10$ to $50 \text{ Hz}$ ; $T_{amb} = 25^\circ C$ )	$E_n$	—	<0.135	<0.135	μV

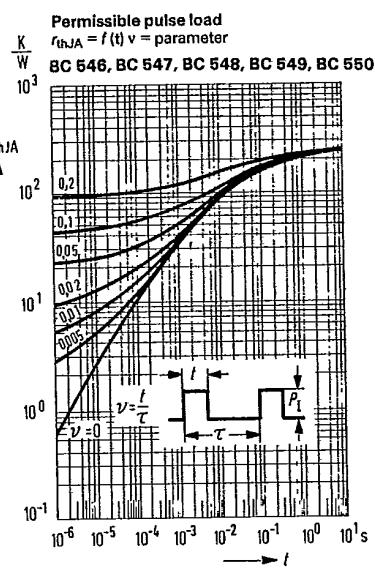
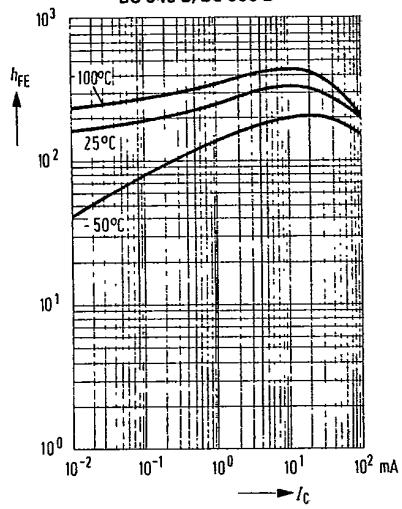
Dynamic characteristics ( $T_{amb} = 25^\circ C$ ) $I_C = 2 \text{ mA}$ ;  $V_{CE} = 5 V$ ;  $f = 1 \text{ kHz}$ 

Type	BC 546 BC 547 BC 548	BC 546 BC 547 BC 548	BC 546 BC 547, BC 549 BC 548, BC 550	BC 548, BC 549, BC 550	
$h_{FE}$ group	VI	A	B	C	
$h_{11e}$	1.2 (0.4 to 2.2)	2.7 (1.6 to 4.5)	4.5 (3.2 to 8.5)	8.7 (6 to 15)	kΩ
$h_{12e}$	2.5	1.5	2	3	$10^{-4}$
$h_{21e}$	110	220	330	600	—
$h_{22e}$	20 (<40)	18 (<30)	30 (<60)	60 (<110)	μS

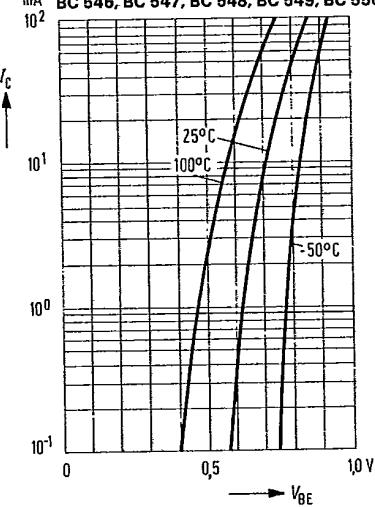
T-29-21

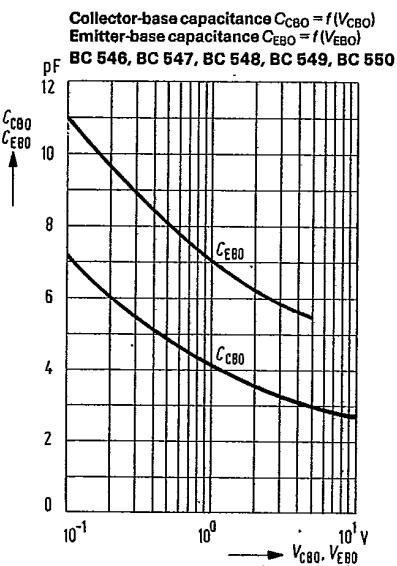
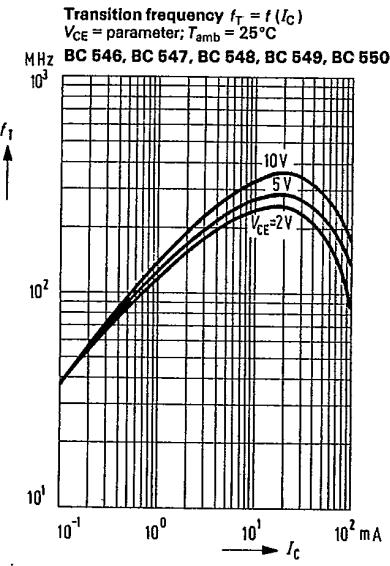
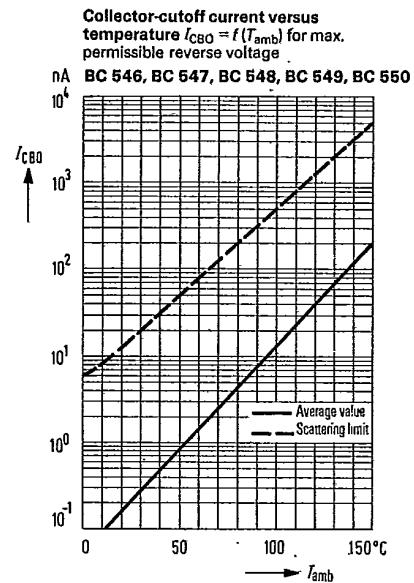
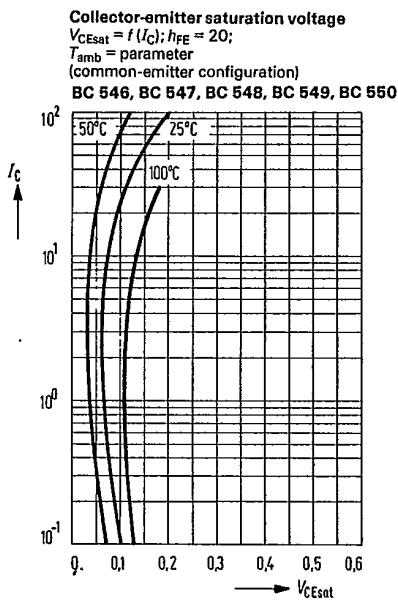


DC current gain  $h_{FE} = f(I_C)$   
 $V_{CE} = 5 \text{ V}$ ;  $T_{amb}$  = parameter  
(common-emitter configuration)  
BC 546 B, BC 547 B, BC 548 B,  
BC 549 B, BC 550 B

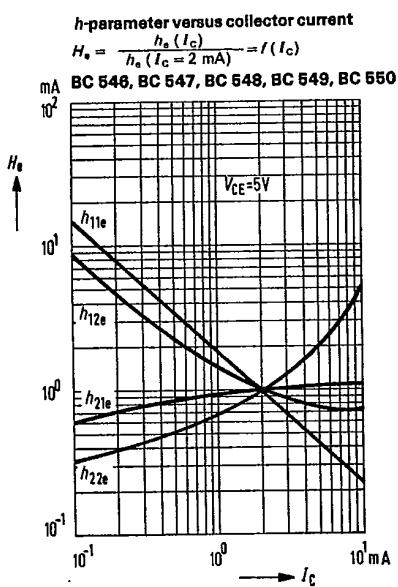


Collector current  $I_C = f(V_{BE})$   
 $V_{CE} = 5 \text{ V}$   
(common-emitter configuration)  
BC 546, BC 547, BC 548, BC 549, BC 550





BC 546 - BC 550



Noise figure  $NF = f(V_{CE})$   
 $I_C = 0.2 \text{ mA}; R_g = 2 \text{ k}\Omega; f = 1 \text{ kHz}$   
 $\Delta f = 200 \text{ Hz}; T_{amb} = 26^\circ \text{C}$

